

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|--|---|------------------|---------|------------------|
| L1 | 0 | (amorphous near silicon) with (molecular near organic near compound) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/09/23 09:28 |
| L2 | 49 | (amorphous near silicon) and (molecular near organic near compound) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/09/23 09:28 |
| S1 | 1601 | 257/40.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/06 16:31 |
| S2 | 1362 | S1 and organic | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/06 16:53 |
| S3 | 184 | S2 and (gate near (oxide insulat\$3 dielectric) near (layer film)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/06 16:47 |
| S4 | 13 | S2 and (gate near oxide near (layer film)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/06 16:53 |
| S5 | 388310 | "257"/\$.ccls. "438"/\$.ccls. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/06 16:52 |
| S6 | 44641 | S5 and organic | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/06 16:53 |
| S7 | 27 | S6 and ((gate near oxide near (layer film)) with (gate near (dielectric insulat\$3) near (layer film)) with (gate near electrode)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/06 16:59 |

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| S8 | 817 | organic adj ((thin adj film adj transistor\$1) TFT\$1) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/06 16:59 |
| S9 | 2 | S8 and ((gate near oxide near (layer film)) with (gate near (dielectric insulat\$3) near (layer film)) with (gate near electrode)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 11:03 |
| S10 | 818 | organic adj ((thin adj film adj transistor\$1) TFT\$1) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 08:53 |
| S11 | 12 | S10 and ((gate near oxide near (layer film)) and (gate near (dielectric insulat\$3) near (layer film)) and (gate near electrode)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 16:08 |
| S12 | 3 | ("5347144" "5946551" "5981970").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/07 11:15 |
| S13 | 6 | ("4724106" "5075738" "5206525" "5347144" "5625199" "5705826").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/07 11:16 |
| S14 | 2 | ("5347144" "5355235").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/07 11:18 |
| S15 | 2 | ("4873556" "5107308").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/07 11:20 |
| S16 | 22 | S10 and (((gate near oxide) (Ta2O3 Al2O3)) and (gate near (dielectric insulat\$3) near (layer film)) and (gate near electrode)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 11:25 |
| S17 | 3 | ("5347144" "5625199" "5981970").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/07 11:33 |
| S18 | 818 | organic adj ((thin adj film adj transistor\$1) TFT\$1) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 18:07 |

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| S19 | 7 | S18 and (molecular near organic near compound) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 18:07 |
| S20 | 12 | ("20030056720" "5402748" "5468519" "5554220" "5736073" "5953828" "6207239" "6232157" "6278127" "6326640" "6337102" "6664137").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/07 17:21 |
| S21 | 13 | ("4021835" "4065781" "5247193" "5315129" "5331183" "5347144" "5350459" "5355235" "5442198" "5500537" "5525811" "5574291" "5612228").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/06/07 17:22 |
| S22 | 5348 | organic adj semiconductor | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 08:56 |
| S23 | 14 | S22 and (molecular near organic near compound) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 18:07 |
| S24 | 2 | (organic adj semiconductor) with (molecular near organic near compound) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 18:31 |
| S25 | 396 | ((intermediate inorganic) adj (material layer film)) with (gate near (oxide insulat\$3) near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 18:43 |
| S26 | 22 | S25 and S22 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 19:09 |
| S27 | 66 | ((intermediate inorganic) adj (material layer film)) with between with (gate near (oxide insulat\$3) near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 19:07 |

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| S28 | 1 | S27 and S22 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 18:43 |
| S29 | 119 | (SiO2 SiN SiON) with between with (gate near (oxide insulat\$3) near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 08:46 |
| S30 | 0 | S29 and S22 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 19:09 |
| S31 | 0 | S29 and S18 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 19:09 |
| S32 | 24 | S29 and organic | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/07 19:10 |
| S33 | 1 | (inorganic SiO SiN SiON) with between with (gate near oxide near (film layer)) with (gate near (insulat\$3 dielectric) near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 08:48 |
| S34 | 18 | (inorganic SiO SiN SiON) same between same (gate near oxide near (film layer)) same (gate near (insulat\$3 dielectric) near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 08:52 |
| S35 | 1316 | (inorganic SiO SiN SiON) and between and (gate near oxide near (film layer)) and (gate near (insulat\$3 dielectric) near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 09:14 |
| S36 | 6 | S35 and (organic adj ((thin adj film adj transistor\$1) TFT\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 08:53 |

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| S37 | 10 | S35 and organic adj semiconductor | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 09:36 |
| S38 | 87 | (inorganic near (material\$1 layer film)) and between and (gate near oxide near (film layer)) and (gate near (insulat\$3 dielectric) near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 09:36 |
| S39 | 85190 | (inorganic near (material\$1 layer film)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 09:35 |
| S40 | 904 | S39 and organic adj semiconductor | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 09:36 |
| S41 | 1 | S40 and (gate near oxide near (film layer)) with (gate near (insulat\$3 dielectric) near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/09/23 06:58 |
| S42 | 10 | S40 and (gate near oxide near (film layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/06/08 09:37 |
| S43 | 51 | (gate near oxide near (film layer)) with (oxidiz\$3 near2 gate near electrode) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/09/23 09:26 |
| S44 | 8 | ("4368523" "4820222" "4938567" "5062690" "5517341" "5532853" "5648826" "5715025").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/09/23 07:20 |
| S45 | 4 | ((5532853") or ("5648826")).PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | OFF | 2005/09/23 07:52 |